AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (original): A process for passivating polysilicon, comprising the following steps:

forming a polysilicon layer; and

annealing using a fluorine-containing gas, a chlorine-containing gas, an oxygen-containing gas, a nitrogen-containing gas, or mixtures thereof to passivate the polysilicon layer.

Claim 2 (original): The process as claimed in claim 1, wherein the annealing step is conducted at a pressure of 1 atm to 20 atm.

Claim 3 (original): The process as claimed in claim 1, wherein the annealing step is conducted at a pressure of 2 atm to 20 atm.

Claim 4 (original): The process as claimed in claim 1, wherein the annealing step is conducted at a temperature of 300°C to 600°C.

Claim 5 (original): The process as claimed in claim 1, wherein the annealing step uses a fluorine-containing gas.

Claim 6 (original): The process as claimed in claim 5, wherein the fluorine-containing gas is NF3, F2, or a mixture thereof.

Claim 7 (original): The process as claimed in claim 1, wherein the step of forming the polysilicon layer comprises:

forming an amorphous silicon layer; and

crystallizing the amorphous silicon layer to convert the amorphous silicon layer into the polysilicon layer.

Claim 8 (original): A process for fabricating a polysilicon thin film transistor, comprising the following steps:

forming a polysilicon layer on a substrate; and

annealing using a fluorine-containing gas, a chlorine-containing gas, an oxygen-containing gas, a nitrogen-containing gas, or mixtures thereof to passivate the polysilicon layer.

Claim 9 (original): The process as claimed in claim 8, wherein the annealing step is conducted at a pressure of 1 atm to 20 atm.

Claim 10 (original): The process as claimed in claim 9, wherein the annealing step is conducted at a pressure of 2 atm to 20 atm.

Claim 11 (original): The process as claimed in claim 8, wherein the annealing step is conducted at a temperature of 300°C to 600°C.

Claim 12 (original): The process as claimed in claim 8, wherein the annealing step uses a fluorine-containing gas.

Claim 13 (original): The process as claimed in claim 12, wherein the fluorine-containing gas is NF3, F2, or a mixture thereof.

Claim 14 (original): The process as claimed in claim 8, wherein the step of forming the polysilicon layer comprises:

forming an amorphous silicon layer; and

crystallizing the amorphous silicon layer to convert the amorphous silicon layer into the polysilicon layer.

Claim 15 (original): The process as claimed in claim 8, wherein after the polysilicon layer is formed, the passivation step is directly performed without forming other films.

Claim 16 (original): The process as claimed in claim 8, further comprising, after the polysilicon layer is formed and before the passivation step, the following step:

forming a gate dielectric layer on the polysilicon layer.

Claim 17 (original): The process as claimed in claim 16, further comprising, after the gate dielectric layer is formed and before the passivation step, the following step:

forming a gate on the gate dielectric layer.

Claim 18 (original): The process as claimed in claim 16, after the gate dielectric layer is formed and before the passivation step, further comprising the following step:

doping the polysilicon layer to form a source/drain region.

Claim 19 (original): The process as claimed in claim 18, wherein the annealing step simultaneously passivates the polysilicon layer and activates the source/drain region .

Claim 20 (New): A process for fabricating a polysilicon thin film transistor comprising:

forming a polysilicon layer on a substrate;
forming a gate dielectric layer on the polysilicon layer;
forming a gate on the gate dielectric layer;
doping the polysilicon layer to form source/drain regions by using the gate as a mask;
forming source/drain electrodes for the source/drain regions respectfully; and
annealing using a fluorine-containing gas, a chlorine-containing gas, an oxygen-containing gas, a nitrogen-containing gas, or mixtures thereof to passivate the polysilicon layer, wherein passivation is performed before the source/drain electrodes are formed.